

2SK60

Silicon N-Channel Junction V-FET

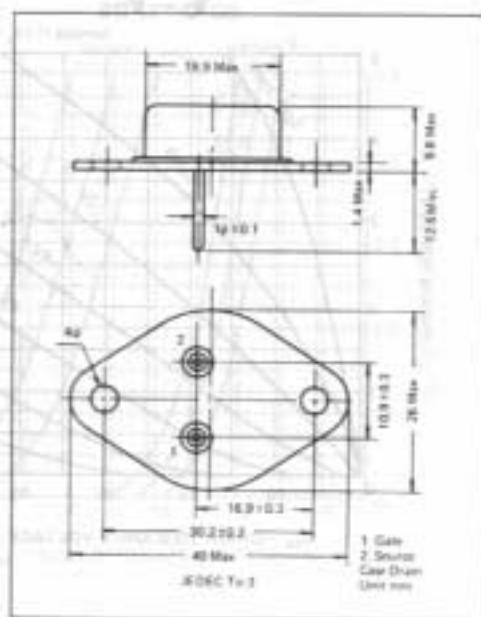
- オーディオパワーアンプ
- HiFi Power Amplifiers
- Complementary to 2SJ18

绝对最大定格 Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

| Characteristics | Symbol | 2SK60 |
|-------------------------|-----------|----------------------------------|
| Drain-to-Gate Voltage | V_{DG0} | 170V |
| Source-to-Gate Voltage | V_{SG0} | *1 |
| Drain Current | I_D | 5A |
| Gate Current | I_G | 0.5A |
| Total Power Dissipation | P_T | 63W ($T_c = 25^\circ\text{C}$) |
| Junction Temperature | T_j | 120°C |
| Storage Temperature | T_{stg} | -50—+150°C |

*1 Source-to-Gate Voltage V_{SG0} 2SK60-2

| | |
|----|------|
| -3 | -30V |
| -4 | -35V |
| -5 | -40V |
| -6 | -45V |
| -7 | -50V |



電気的特性 Electrical Characteristics $T_a = 25^\circ\text{C}$

| Characteristics | Symbol | Conditions | Min. | Typ. | Max. | Unit |
|-------------------------------------|----------------|---|------|------|------|---------------------------|
| Drain Cutoff Current | I_{DG0} | $V_{DG} = 100\text{V}, I_S = 0$ | | 0.1 | 100 | μA |
| Source Cutoff Current | I_{SG0} | $V_{GS} = 30\text{V}, I_D = 0$ | | 0.1 | 100 | μA |
| Drain-to-Source On-State Voltage | V_{DS} | $I_G = 0.2\text{A}, I_D = 3\text{A}, t = 100\text{ms}$ | | | 10 | V |
| Pinch-off Voltage | V_p | $V_{DS} = 60\text{V}, I_D = 100\text{mA}$ | -7.5 | -18 | -25 | V |
| Input Capacitance | C_{iss} | $V_{DS} = -15\text{V}, V_{GS} = 0\text{V}, f = 1\text{MHz}$ | | 190 | | pF |
| Gain Bandwidth Product | f_T | $V_{DS} = 20\text{V}, I_D = 0.5\text{A}$ | | 20 | | MHz |
| Voltage Amplification Ratio | μ | $V_{DS} = 20\text{V}, I_D = 1\text{A}, f = 1\text{kHz}$ | | 4 | | |
| Output Resistance | r_D | $V_{DS} = 20\text{V}, I_D = 1\text{A}, f = 1\text{kHz}$ | | 16 | | Ω |
| Area of Safe Operation | ASO | $V_{DS} = 50\text{V}, t = 100\text{ms}, T_c = 25^\circ\text{C}$ | 2.5 | | | A |
| Junction-to-Case Thermal Resistance | θ_{j-c} | | | | 1.5 | $^\circ\text{C}/\text{W}$ |